

MOSFET DRIVER WITH PROTECTION AND DIAGNOSTIC

Features

- Bootstrap and charge pump
- Over temperature shutdown (with Ptc interface)
- Short circuit protection (Vds detection)
- Reverse battery protection (turns On the MOSFET)
- Diagnostic
- ESD protection

Description

The AUIR3200S is a high side mosfet driver for very low Rdson automotive application. It offers over-current, over-temperature protection and diagnostic. The over-current protection is done by monitoring the Vds voltage, the threshold is programmable by external resistor. The over-temperature protection uses a thermal sensor. The AUIR3200S offers diagnostic on the input pin.

Product Summary

Operating voltage 6-36V
Vgate 6V

Package

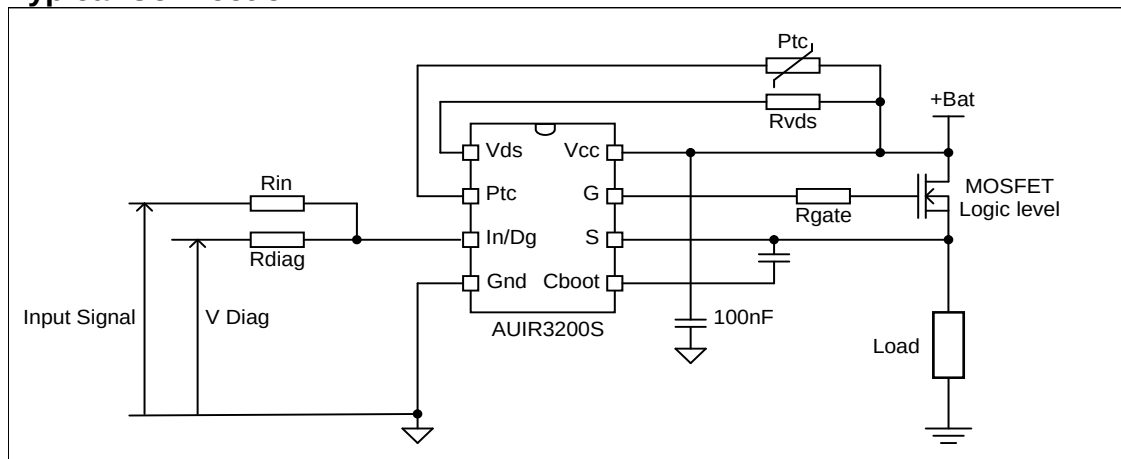


SO8

Ordering Information

Base Part Number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIR3200S	SOIC-8 leads	Tube	95	AUIR3200S
		Tape and Reel	2500	AUIR3200STR

Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are referenced to Ground lead. (Tj= -40°C..150°C unless otherwise specified).

Symbol	Parameter	Min.	Max.	Units
Vcc-gnd	Maximum Vcc voltage	-0.3	60	V
Vcc-Vds	Maximum Vds pin voltage	-0.3	5.5	
Vcc-Vptc	Maximum Ptc pin voltage	-0.3	5.5	
Vin-gnd	Maximum IN pin voltage	-0.3	5.5	
Vcc-Vs	Maximum S pin voltage	-0.3	60	
Vcboot-Vs	Maximum Cboot pin voltage	-0.3	8	
Vcc cont.	Maximum continuous Vcc voltage	—	36	
Tj max.	Maximum operating junction temperature	-40	150	°C
	Maximum storage temperature	-55	150	
Tsoldering	Soldering temperature (10 seconds)	—	300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
Rth	Thermal resistance junction to ambient	100	—	°C/W

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
VIH	High level input voltage	2.7	5.5	V
VIL	Low level input voltage	0	0.9	
Rin	Recommended resistor in series with IN pin	10	15	KΩ
Rdiag	Recommended resistor in series with Diag pin	4	15	

Static Electrical Characteristics

T_j=-40°C..125°C, V_{cc}=6-36V (unless otherwise specified), typical value are given for V_{cc}=14V and T_j=25°C.

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{cc op.}	Operating voltage range	6	—	36	V	
I _{cc Off}	Supply current in sleep mode T _j =25°C	—	1	5	μA	V _{cc} =14V, V _{in} =0V
I _{cc On}	Supply current when On	—	10	15	mA	V _{in} =5V, V _{ptc} =V _{bat} , V _{ds} =V _{bat}
V _{IH}	IN High threshold voltage	—	2	2.6	V	
V _{IL}	IN Low threshold voltage	0.5	1.7	2.1		
I _{n hyst.}	Input hysteresis	0.2	0.5	1		
I _{in on}	On state input current	—	33	50	μA	V _{in} =5V
V _{gs}	Gate output voltage	5	5.7	—	V	I _{gs} =0μA
V _{gs rev}	Gate output voltage during reverse battery T _j =25°C	4.5	5.6	—		I _{gs} =50μA, V _{bat} =14V
V _{in, off}	Input voltage when the part is in fault mode	—	0.25	0.4		I _{dg} =300μA

Protection Characteristics

T_j=-40°C..125°C, V_{cc}=6-36V (unless otherwise specified), typical value are given for V_{cc}=14V and T_j=25°C.

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _{vds}	V _{ds} current reference	0.7	0.8	0.91	mA	V _{cc} -V _{ds} =0V, T _j =-40°C
		0.84	0.93	1.05		V _{cc} -V _{ds} =0V, T _j =25°C
		1	1.15	1.33		V _{cc} -V _{ds} =0V, T _j =125°C
V _{ds offset}	V _{ds} comparator offset	-10	0	10	mV	
T _{blank on}	V _{ds} detection blanking time during turn on	15	22	35	μs	
V _{ptc}	PTC comparator voltage threshold (V _{cc} -V _{ptc})	1.5	2	2.5	V	V _{in} =5V, V _{cc} =14V
R _{ptc}	Pull down resistor on the PTC pin	4	10	20	kΩ	
T _{diag}	Diagnostic time	—	10	—	ms	see figure 2
T _{sleep}	Time to enter in sleep mode	7	15	30		see figure 2
T _{reset}	Time to enter in sleep mode and reset the fault	—	5	—		see figure 2
T _{wkp}	Time to leave the sleep mode	0.5	—	—	μs	R _{in} =10k see figure 3 & 4
T _{pwr on rst}	Power on reset duration T _j =25°C	40	100	200	μs	
UV	Under voltage threshold	—	5.2	5.9	V	
T _{UV hold}	Time to keep UV detection active	150	350	600	μs	

Switching Characteristics

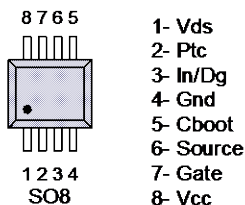
T_j=−40...125°C, V_{cc}=6...36V (unless otherwise specified), typical value are given for V_{cc}=14V and T_j=25°C.

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
T _{don}	Turn-on delay to 20% of V _{gs}	—	1.6	—	μs	Q _g =220nC, R _{gate} =0Ω
T _r	Rise time 20% to 80% of V _{gs}	—	1	—		
T _{doff}	Turn off delay time to 80% of V _{gs}	—	2	—		
T _f	Fall time from 80% to 20% of V _{gs}	—	1	—		
I _{gs+}	Gate output high pulsed current	100	160	—	mA	V _{gs} =0V
I _{gs-}	Gate output low pulsed current	100	130	—		V _{gs} =5.7V
I _{boot}	Cboot capacitor charge current	0.35	0.8	—	A	
V _{boot-Source}	Cboot capacitor charge voltage	5.6	6	—	V	

True Table

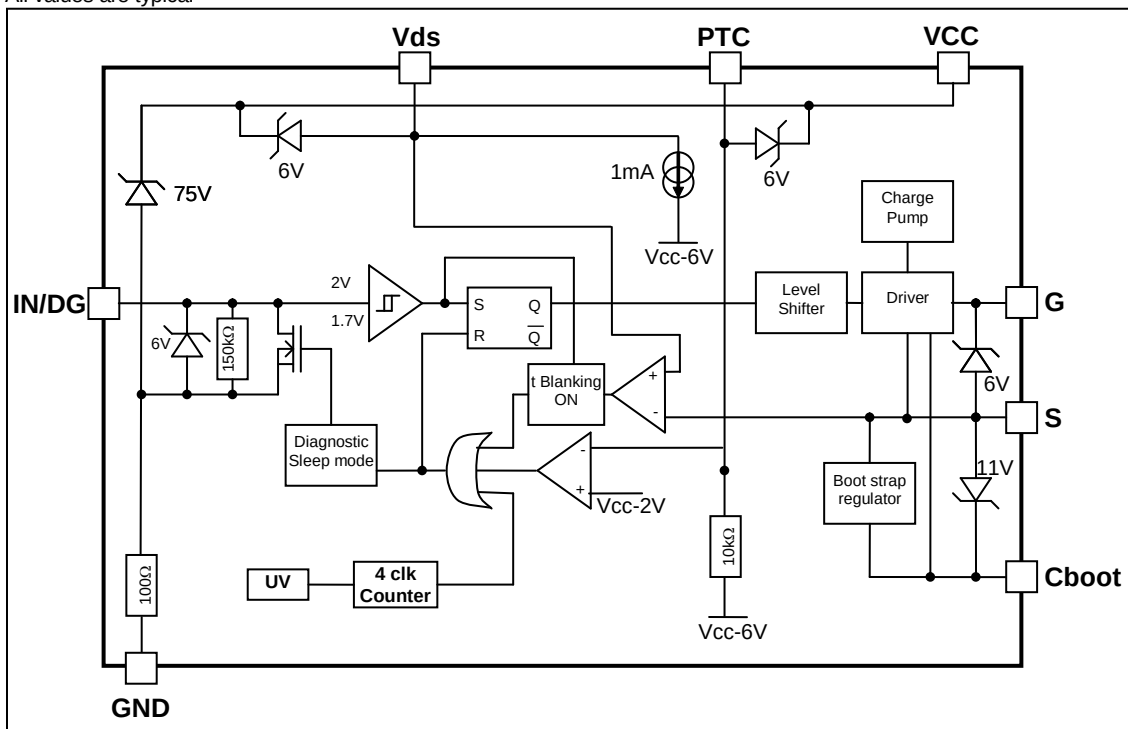
Operating Conditions	IN	OUT	DG
Normal ON	H	H	H
Normal OFF	L	L	L
Short circuit to Gnd	H	L	L
Short circuit to Gnd	L	L	L
Over-temperature	H	L	L
Over-temperature	L	L	L

Lead Assignments



Functional Block Diagram

All values are typical



Over-current protection

The over-current protection is done by monitoring the Vds voltage of the Mosfet. The threshold is adjusted by connecting the appropriate resistor between Vcc and Vds pin. Below the formula to set the appropriate over-current threshold:

$$I_{sd_threshold} = \frac{I_{vds} \times R_{vds}}{R_{dsOn}}$$

The Ivds has a positive temperature coefficient to compensate the positive temperature coefficient of the RdsOn of the Mosfet.

The above formula is only valid when the Mosfet is fully ON. Therefore during the turn on of the MOSFET, the time 'Tblank on' disable the vds protection until the Mosfet is fully On.

Over-temperature protection

The temperature protection uses a PTC sensor connected to the tab or the drain of the Mosfet depending on the mounting. The purpose is to maximize the thermal interface between the sensor and the junction. The PTC sensor, the Vds threshold and the Mosfet must be chosen in order to not exceed the maximum junction temperature of the Mosfet during a short circuit.

Protection is evaluated by switching the Mosfet on different currents and by evaluating the junction temperature when the Mosfet is switched off by the protections. This gives the following drawing. For high impedance short circuit, Vds is smaller than Vds threshold, so the over-temperature will act. For low impedance short circuit, the Vds protection will switch off the Mosfet. At the transition current between the 2 protections the junction temperature of the Mosfet is the maximum and should be lower than the maximum rating.

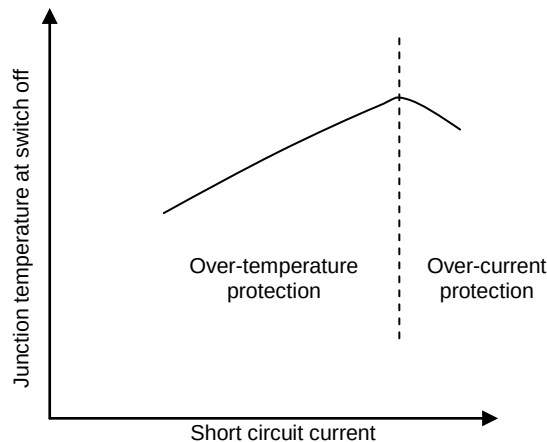


Figure 1

Sleep_mode / Diagnostic

Sleep_mode block manages the diagnostic and the sleep_mode. The device enters in sleep mode if input is inactive during a delay higher than T_{sleep} .

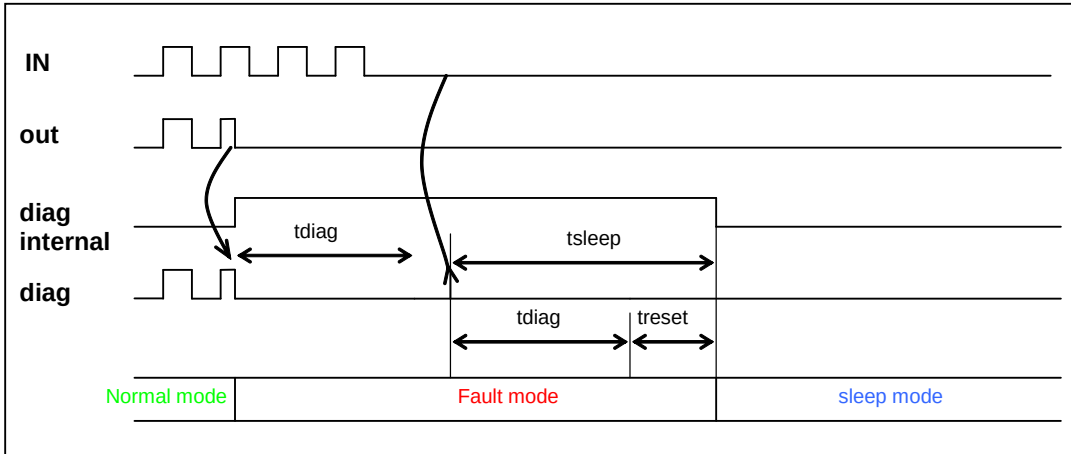


Figure 2

Wake up sequence

To wake up the part from the sleep mode, the input must be activated at least during T_{wkp} , then the bootstrap regulator is switched on and the bootstrap capacitor is charged. The output will not be activated during T_{pw} on rst.

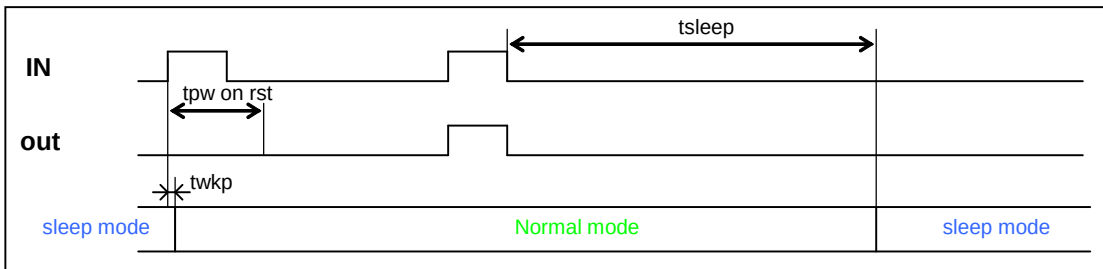


Figure 3

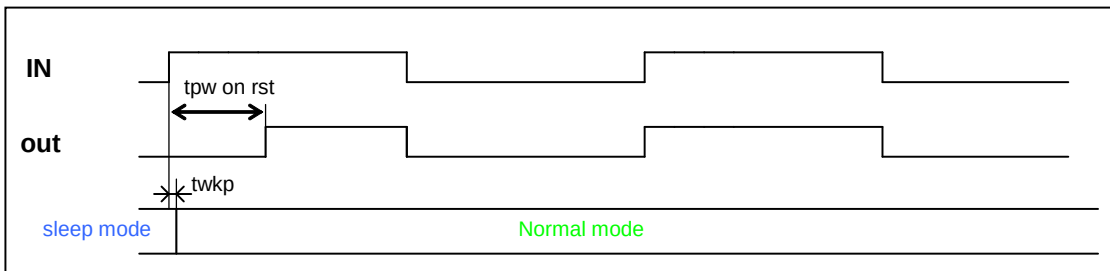


Figure 4

Bootstrap

The bootstrap capacitor provides the necessary current to the driver in order to charge the gate capacitor to the right voltage level.

A design rule to select the bootstrap capacitor value is to choose 10 times the gate capacitance.

You can find in the Mosfet datasheet 'Qg max' for a specific Vgs.

Use this equation to calculate Cboot value:

$$C_{boot} = 10 \times \frac{Q_{g \max}}{V_{gs}}$$

The AUIR3200S integrates a bootstrap regulator to maintain a fixed voltage (Vboot=6V) on the bootstrap capacitor for any battery voltage.

The regulator is off during the sleep mode to reduce the current consumption.

The power on reset is necessary to charge the bootstrap capacitor before turns on the power mosfet. The bootstrap capacitor gets its charge through the load. So the time to charge it depends of the load.

But the power on reset doesn't monitor the bootstrap capacitor voltage. Its time is set internally to allow starting the most of load without implement a special sequence:

The power on reset is long enough to charge the bootstrap capacitor before turns on the power mosfet.

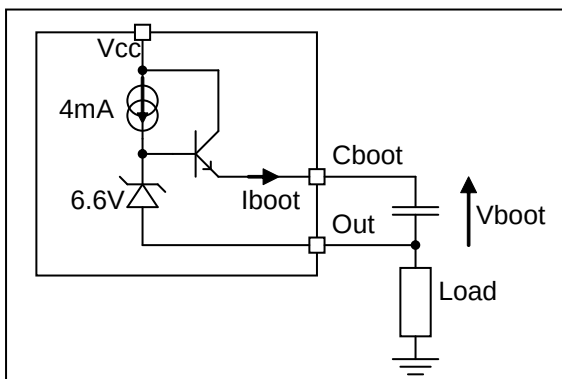


Figure 5

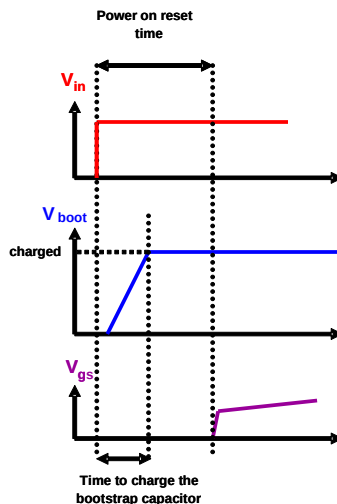


Figure 6

If the inductance of the load is too important, the power on reset is not enough long to charge completely the bootstrap capacitor before turns on the power mosfet.

So the micro-processor need to implement a special sequence to start the device without activates the output power mosfet.

The micro-processor send one short pulse ($T_{wkp\ min} < \text{short pulse} < T_{pwr_on_rst}$) then wait for the bootstrap capacitor is totally charged and after provide the appropriate duty cycle.

The bootstrap charge depends of the battery voltage, the bootstrap capacitor value and the inductance load value.

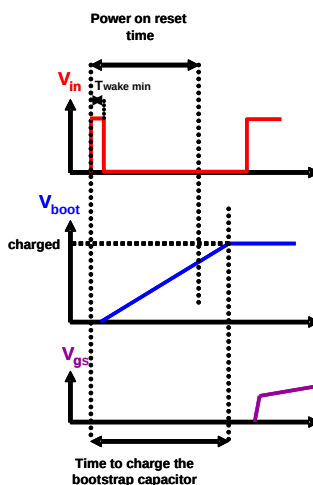


Figure 7

IN frequency and duty cycle

The V_{ds} protection is not active if the time ON is lower than $T_{blank\ on}$.
So the minimum time ON (t_{on}) is ' $T_{blank\ on\ max}$ ' to be sure that this protection will be active.

The times OFF (t_{off}) needs to be setup for assure that the capacitor bootstrap will be recharged up to 6V. The bootstrap time charge depends of the bootstrap capacitor value and the inductance load value.

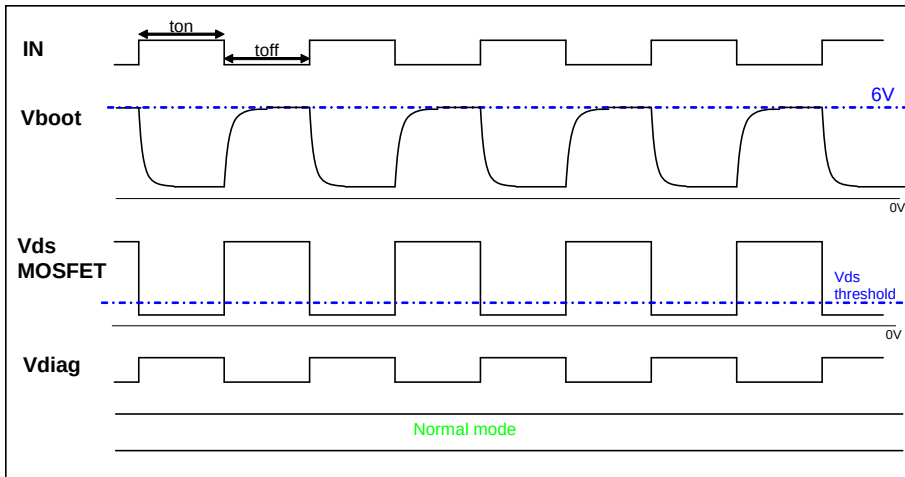


Figure 8

If the capacitor is discharged at the turn ON of the MOSFET, the AUIR3200S will detect a fault (VDS protection) after $T_{blank\ ON}$ because the MOSFET won't be fully ON.

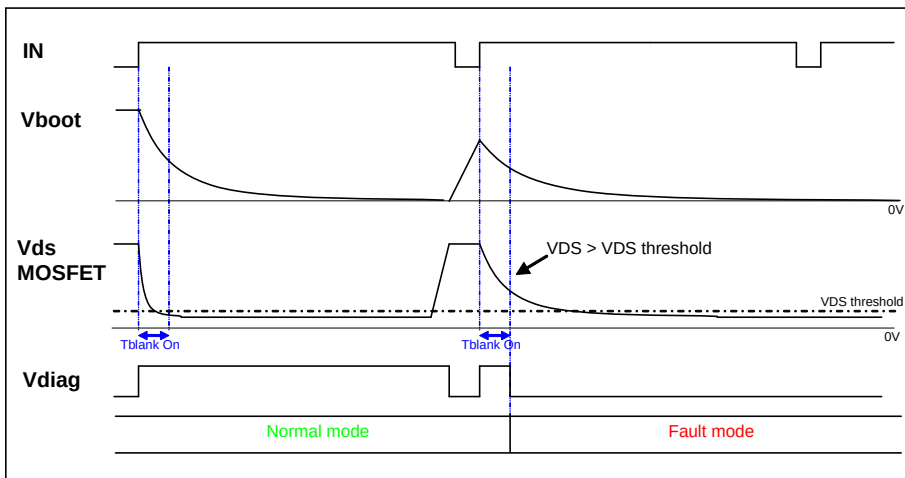


Figure 9

Under voltage protection in short-circuit mode

During short circuit condition, it may happen that the supply voltage drops below the under voltage before the short is detected by the Vds protection due to the blanking time 'Tblank on'.

In under voltage condition the AUIR3200S turns off the MOSFET. The time 'Tblank On' is reset.

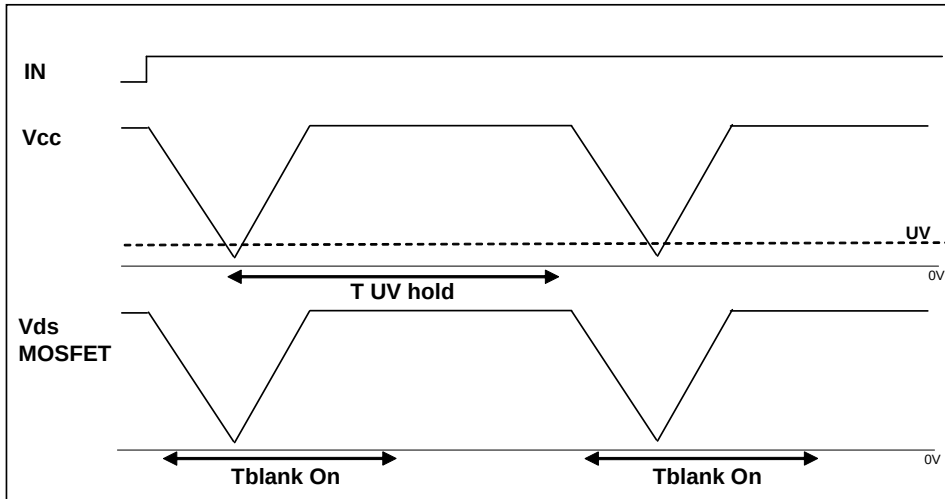


Figure 10

In order to detect the short circuit condition, the AUIR3200S has a counter and after 4 'under voltage' detections, the part is latched and the fault diagnostic is activated. The counter is reset when the part goes to sleep mode.

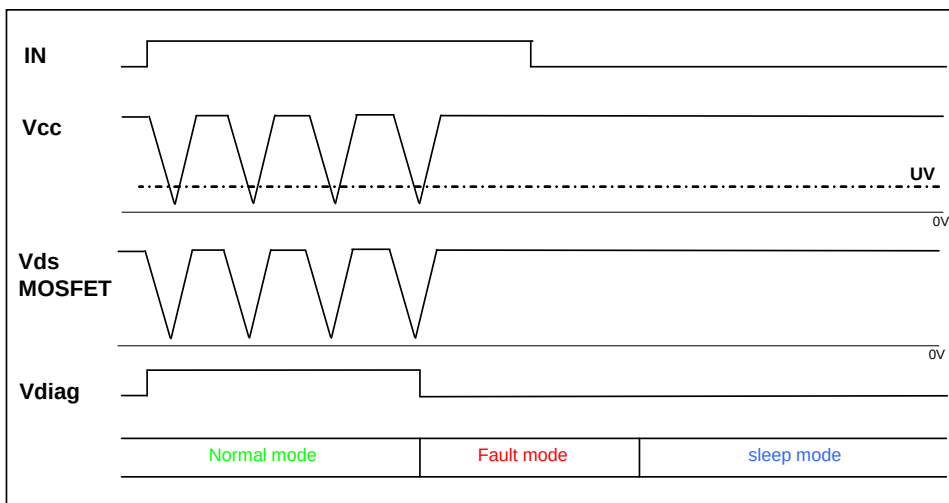


Figure 11

PWM operation ($T_{on} < T_{blank\ on}$)

PWM operation is also possible. The bootstrap feature allows fast switching. When the T_{on} is shorter than the $T_{blank\ on}$, the V_{ds} protection is no longer activated. In order to protect the Power Mosfet, the AUIR3200S integrates a counter which is incremented by the input signal and reset when the V_{ds} voltage is below the V_{ds} threshold. The counter latches off the AUIR3200S after 4 activations. During PWM operation ($T_{on} < T_{blank\ on}$) on a short circuit, the V_{ds} is always above the V_{ds} threshold and 4 activations on the input will latch the AUIR3200S and the fault diagnostic is activated.

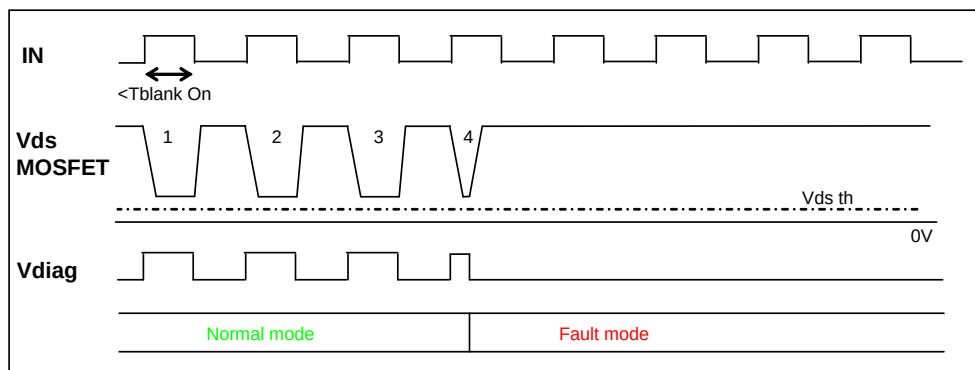


Figure 12

Parameters curves: typical value

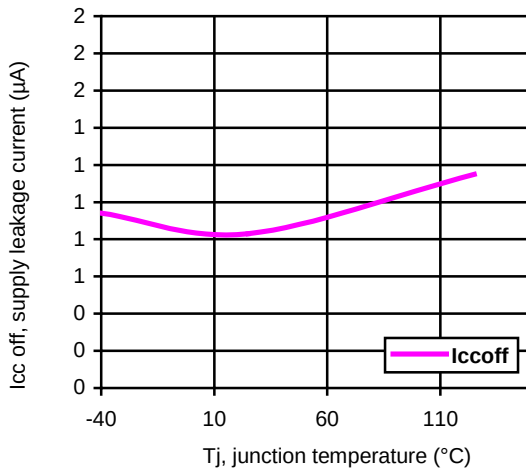


Figure 13: $I_{cc\text{ off}}$ (μA) Vs T_j ($^{\circ}\text{C}$) $V_{cc}=14\text{V}$, $V_{in}=0\text{V}$

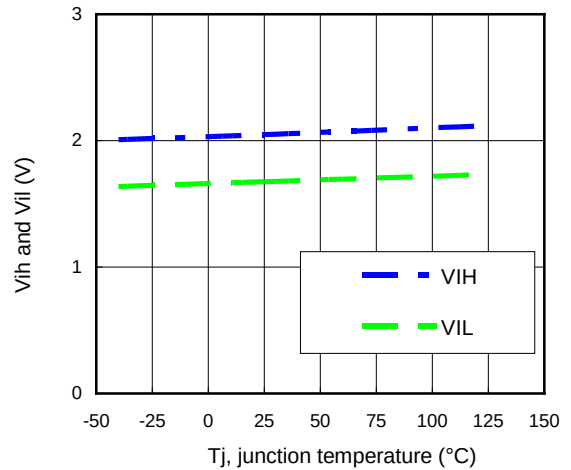


Figure 14: V_{ih} and V_{il} (V) Vs T_j ($^{\circ}\text{C}$)

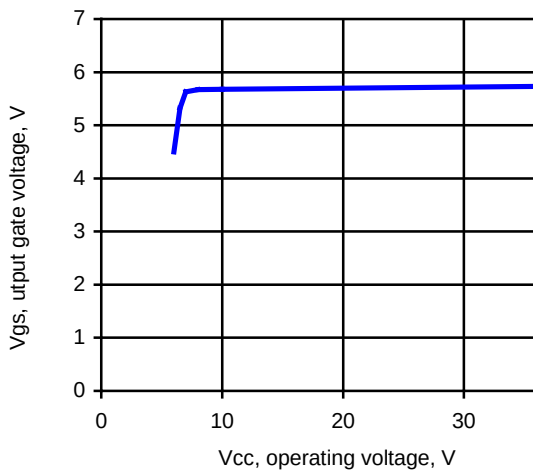
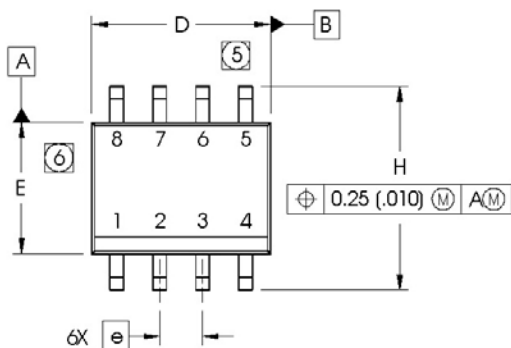


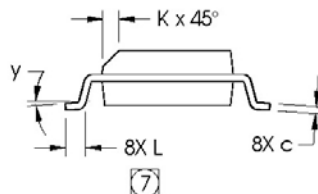
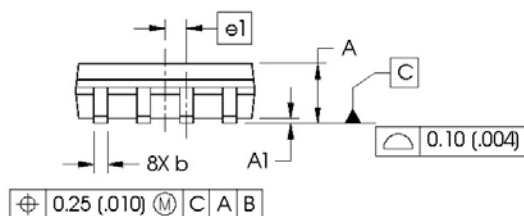
Figure 15: V_{gs} vs V_{cc} with $I_{vgs}=50\mu\text{A}$

Case Outline – SO8

Dimensions are shown in millimeters (inches)



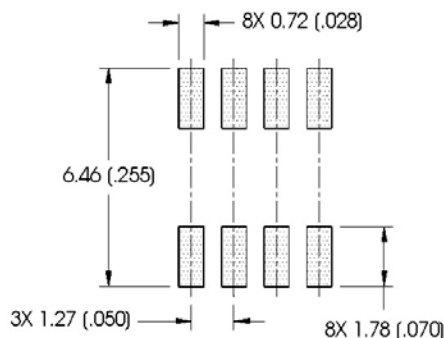
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



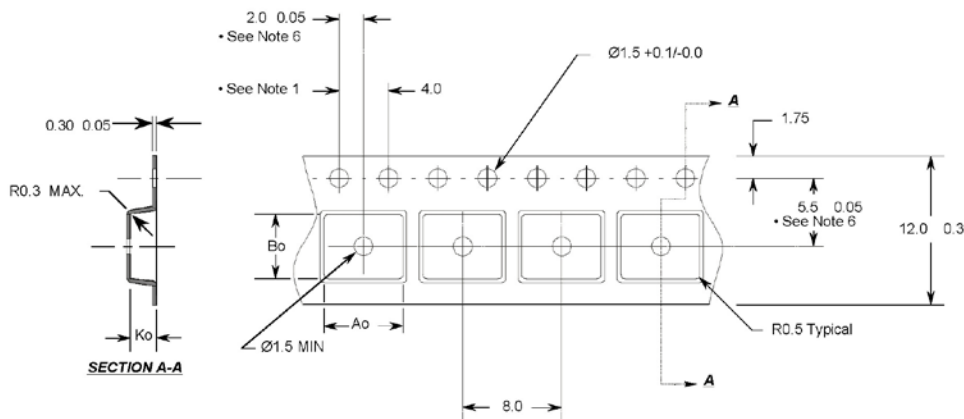
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



Tape & Reel SO8

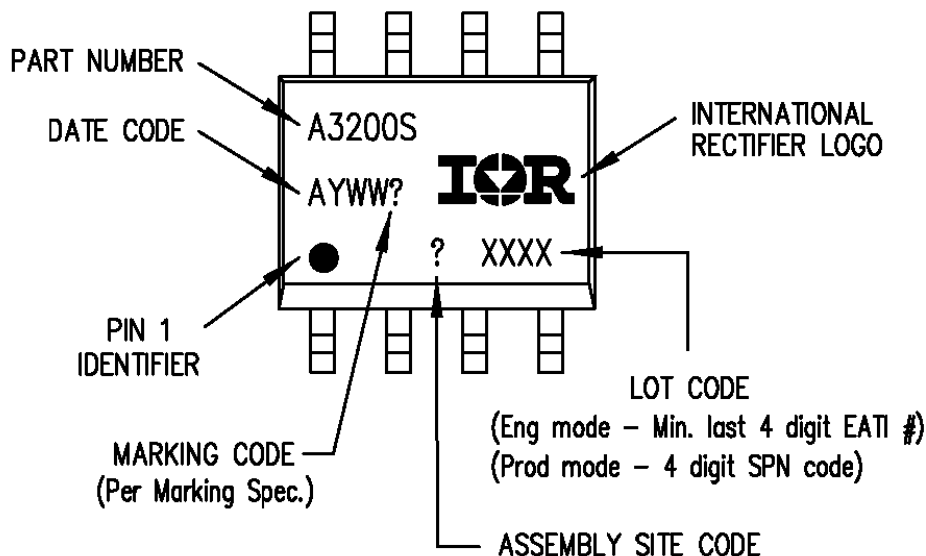

Notes:

1. 10 sprocket hole pitch cumulative tolerance 0.2
2. Camber not to exceed 1mm in 100mm
3. Material: Black Conductive Advantek Polystyrene
4. A_o and B_o measured on a plane 0.3mm above the bottom of the pocket
5. K_o measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

$A_o = 6.4 \text{ mm}$
 $B_o = 5.2 \text{ mm}$
 $K_o = 2.1 \text{ mm}$

- All Dimensions in Millimeters -

Part Marking Information



TOP MARKING (LASER)

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q100)	
		Comments: This family of ICs has passed an Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SOIC8N	MSL2 260°C (per IPC/JEDEC J-STD-020)
ESD	Machine Model	Class M1B(+/-100V) (per AEC-Q100-003)	
	Human Body Model	Class H1C (+/-1500V) (per AEC-Q100-002)	
	Charged Device Model	Class C4 (+/-1000V) (per AEC-Q100-011)	
IC Latch-Up Test		Class II, Level A (per AEC-Q100-004)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site <http://www.irf.com/>

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For technical support, please contact IR's Technical Assistance Center
<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

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Revision History

Revision	Date	Notes/Changes
A	November 2, 2012	Initial release